New Release

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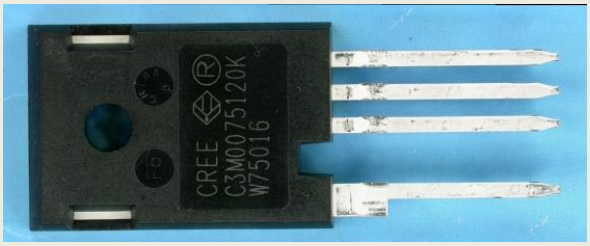
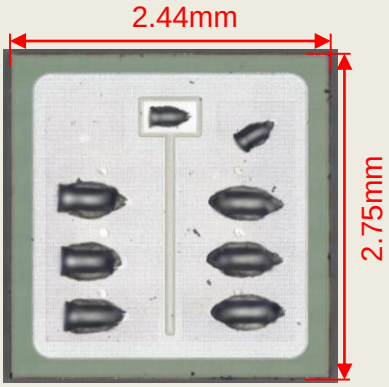
ANALYSIS REPORT THE WOLFSPEED C3M0075120K 3rd GENERATION 1200V SiC POWER MOSFET

February 2018. LTEC Corporation released a detailed structure and process analysis report of this 1200V silicon carbide MOSFET, the 3rd product using a planer-gate transistor design. This device has shrunk die size (35%) and reduced Ron(30%) relative to 2nd gen product.



Package top view



Die top view

Device features

- Max. operating voltage: 1200V, rated DC Drain current ID=30A at Tj=25℃
- Low specific ON-resistance, RON x A= 503mΩ x mm^2

The report has two individually purchasable sections: an 67-page Structure Analysis, and a 28-page Process Analysis section. The Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the impurity concentration of the epitaxial layer.

Structure analysis report:	**$4,600**
Process analysis report:	**$4,600**

Note: The listed report price may not be accurate as it decreases over time.
Please contact us for current report pricing : **info@ltecusa.com**

17G-0010-1

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